

## Publikationen 1995

**Angermann, H.; Kliefoth, K.; Füssel, W.; Flietner, H.:** Defect Generation at Silicon Surfaces during Etching and Initial Stage of Oxidation. Micro-electronic Engineering 28 (1995), pp. 51-54 -g

**Brehme, S.; Elstner, L.; Fenske, F.; Henrion, W.; Hoffman, V.; Poschenrieder, M.; Schäfer, F.; Selle, B.; Sieber, I.:** Doped Magnetron Sputtered ZnO:Al Films as Window Layers in Silicon Based Photovoltaic Heterojunctions Cells. Proc. of the 13th European Photovoltaic Solar Energy Conference, Eds.: W. Freiesleben, W. Palz, H. A. Ossenbrink, P. Helm, Stephens & Ass., Bedford, UK (1995), pp. 1746-1749

**Dittrich, T.; Flietner, H.:** Investigation of Electronic Properties of Porous Silicon by the Pulsed Surface Photovoltage Technique. Mat. Res. Soc. Symp. Proc., 358 (1995), pp. 581-586

**Dittrich, T.; Kashkarov, P. K.; Konstantinova, E. A.; Timoshenko, V. Y.:** Relaxation Mechanisms of Electronic Excitation in Nanostructures of Porous Silicon. Thin Solid Films 255 (1995), pp. 74-77

**Dittrich, T.; Konstantonova, E. A.; Timoshenko, V. Y.:** Influence of Molecule Adsorption on Porous Silicon Photoluminescence. Thin Solid Films 255 (1995), pp. 238-241

**Dittrich, T.; Rauscher, S.; Bitzer, T.; Aggour, M.; Flietner, H.; Lewerenz, H. J.:** Electronic Properties of n-Si(111) during Electrochemical Surface Transformation toward H-Termination. J. Electrochem. Soc. 142 (1995), pp. 2411-2413

**Dittrich, T.; Rauscher, S.; Timoshenko, V. Y.; Rappich, J.; Sieber, I.; Flietner, H.; Lewerenz, H. J.:** Ultrathin Luminescent Nanoporous Silicon on n-Si: pH Dependent Preparation in Aqueous NH<sub>4</sub>F Solutions. Appl. Phys. Lett. 67 (1995), pp. 1134-1136 -g

**Dittrich, T.; Timoshenko, V. Y.; Kashkarov, P. K.; Flietner, H.:** Influence of the Oxidation Process on the Luminescence of the HF-Treated Porous Silicon. Thin Solid Films 255 (1995), pp. 149-151

**Fenske, F.; Lange, H.; Oertel, G.; Reinsperger, G.-U.; Schumann, J.; Selle, B.:** Characterization of Semiconducting Silicide Films by Infrared Vibrational Spectroscopy. Proc. of the Symp. "IUMRS-ICEM '94", Eds.: L. J. Chen, T. T. Tsong, S. C. Sun, Vol.1, (1995), pp. 155-160

**Flietner, H.:** Passivity and Electronic Properties of the Silicon/Silicondioxide Interface. Materials Science Forum 185-188 (1995), pp. 73-82

**Füssel, W.; Eschrich, H.; Elstner, L.; Schmidt, M.; Sinh, N.D.; Henrion, W.;**

◀ [HMI Solarenergieforsch.](#)

◀ [Silizium Photovoltaik](#)

### Publikationen SE1

1992 bis 2002:

[Jahrgang 2002](#)

[Jahrgang 2001](#)

[Jahrgang 2000](#)

[Jahrgang 1999](#)

[Jahrgang 1998](#)

[Jahrgang 1997](#)

[Jahrgang 1996](#)

[Jahrgang 1995](#)

[Jahrgang 1994](#)

[Jahrgang 1993](#)

[Jahrgang 1992](#)

**Angermann, H.; Flietner, H.; Henschel, R.; Kragler, G.; Willeke, G.:** Doped SIPOS (SiOx)/c-Si Heterojunction for Heteroemitter Silicon Solar Cells. Proc. of the 13th European Photovoltaic Solar Energy Conference, Eds.: W. Freiesleben, W. Palz, H. A. Ossenbrink, P. Helm, Stephens & Ass., Bedford, UK (1995), pp. 45-48

**Füssel, W.; Elstner, L.; Eschrich, H.:** Heteroemitter für Silizium-Solarzellen. Statusreport 1995 Photovoltaik, Eds.: BMFT, BEO, KFA Jülich

**Heinrich, A.; Gladun, C.; Burkov, A.; Tomm, Y.; Brehme, S.; Lange, H.:** Thermopower and Electrical Resistivity of  $\beta$ -FeSi<sub>2</sub> Single Crystals doped with Cr, Co and Mn. In: "Proc. of the XIV International Conference on Thermoelectrics", Eds.: M. V. Vedernikov, M. I. Fedorov, A. E. Kaliazin, A. F. Ioffe Physical-Technical Institute, St. Petersburg, Russia (1995), pp. 259-263

**Irmscher, K.; Gelhoff, W.; Tomm, Y.; Lange, H.:** Iron Group Impurities in Semiconducting Iron Disilicide. Scitec Publications, In: Proc. of the 6th Autumn Meeting "Gettering and Defect Engineering in Semiconductor Technology" GADEST '95; Eds.: H. Richter, M. Kittler, C. Claeys, Solid State Phenomena, 47-48 (1995), pp. 287-292

**Kolter, M.; Eschrich, H.; Elstner, L.; Beneking, C.; Wagner, H.:** Electrical Properties of (n)a-Si:H/(p)c-Si Solar Cells. Proc. of the 13th European Photovoltaic Solar Energy Conference, Eds.: W. Freiesleben, W. Palz, H. A. Ossenbrink, P. Helm, Stephens & Ass., Bedford, UK (1995), pp. 1526-1559

**Krankenhagen, R.; Schmidt, M.; Koynov, S.; Grebner, S.; Henrion, W.; Sieber, I.; Schwarz, R.:** Absorption and Transport Properties of Microcrystalline Si-Films Prepared by CC CVD. Proc. of the 13th European Photovoltaic Solar Energy Conference, Eds.: W. Freiesleben, W. Palz, H. A. Ossenbrink, P. Helm, Stephens & Ass., Bedford, UK (1995), pp. 1700-1703

**Krankenhagen, R.; Schmidt, M.; Grebner, S.; Poschenrieder, M.; Henrion, W.; Sieber, I.; Koynov, S.; Schwarz, R.:** Correlation between Structural, Optical and Electrical Properties of  $\mu$ c-Si Films. Proc. of the 13th European Photovoltaic Solar Energy Conference, Eds.: W. Freiesleben, W. Palz, H. A. Ossenbrink, P. Helm, Stephens & Ass., Bedford, UK (1995), p. 1012

**Lange, H.:** Phase Transitions in Nanostructured Transition Metal Silicides by the Example of Iron Disilicide. In: Physics, Chemistry, and Application of Nanostructures, Eds.: V. E. Borisenko, A. B. Filonov, S. V. Gaponenko, V. S. Gurin, Belorussian State University of Informatics and Radioelectronics, Minsk, Weißrußland (1995), pp. 25-32

**Lange, H.:** Semiconducting Transition Metal Silicide Films - Preparation, Properties and Possible Applications. In: "CAS '95, Proceedings of the International Semiconductor Conference", Ed.: S. Iordanescu, 18th Edition, Sinaia, Romania, (1995), pp. 531-541

**Libezny, M.; Poortmans, J.; Vermeulen, T.; Nijs, J.; Amesz, P.H.; Herz, K.; Powalla, M.; Reinsperger, G.-U.; Schmidt, M.; Hoffmann, V.; Lange, H.:**  $\beta$ -FeSi<sub>2</sub>/Si Heterojunction Properties and Their Dependence on the  $\beta$ -FeSi<sub>2</sub> Preparation Method. Proc. of the 13th European Photovoltaic Solar Energy Conference, Eds.: W. Freiesleben, W. Palz, H. A. Ossenbrink, P. Helm, Stephens & Ass., Bedford, UK (1995), pp. 1326-1329

Losada, B. R.; Moehlecke, A.; Ruiz, J.M.; Luque, A.; Wollweber, J.; Abrosimov, N.; Schulz, D.; Schröder, W.; Rossolenko, S.; Schöpke, A.: Development of Solar Cells on Monocrystalline Alloys of Si<sub>1-x</sub>G<sub>x</sub>. Proc. of the 13th European Photovoltaic Solar Energy Conference, Eds.: W. Freiesleben, W. Palz, H. A. Ossenbrink, P. Helm, Stephens & Ass., Bedford, UK (1995), pp. 925-928

Müller, P.; Conrad, E.; Omstead, T. R.; Kember, P.: Deposition of Poly-Si and Si-Based Dielectrics by ECRCVD and RTCVD. Proc. of the 13th European Photovoltaic Solar Energy Conference, Eds.: W. Freiesleben, W. Palz, H. A. Ossenbrink, P. Helm, Stephens & Ass., Bedford, UK (1995), pp. 1742-1745

Panzner, M.; Mai, H.; Schöneich, B.; Selle, B.; Lange, H.; Henrion, W.; Wittke, T.; Lenk, A.; Resiak, A.; Grötzschel, R.: Synthesis of  $\beta$ -FeSi<sub>2</sub>-Films by Pulsed Laser Deposition. In: "Proceedings of the First International Symposium on Semiconductor Processing and Characterization with Lasers", Eds.: M. Brieger, H. Dittrich, M. Klose, H. W. Schock, J. Werner, Trans Tech Publications, Schweiz, 173-174 (1995), pp. 123-128

Rappich, J.; Aggour, M.; Rauscher, S.; Jungblut, H.; Lewerenz, H.J.: Electrochemical Surface Conditioning of Silicon. Appl. Surf. Science 335 (1995), pp. 160-165

Rappich, J.; Lewerenz, H. J.: Electrochemical and Electronic Passivation by Hydrogenation of n-Si(111). Materials Science Forum 185-188 (1995), pp. 83-90 -g

Rappich, J.; Lewerenz, H. J.: In-Situ Fourier Transform Infrared Investigation on the Electrolytic Hydrogenation of n-Si(111). J. Electrochem. Soc., Vol. 142, (1995), pp. 1233-1237 -g

Rauscher, S.; Dittrich, T.; Aggour, M.; Rappich, J.; Flietner, H.; Lewerenz, H. J.: Reduced Interface State Density after Photocurrent Oscillations and Electrochemical Hydrogenation of n-Si(111): A SPV Investigation. Appl. Phys. Letters 66 (1995), pp. 3018-3020

Scharf, S.; Schmidt, M.; Bräunig, D.: Influence of Tunneling on Trapping Kinetics in Thin Layers. Materials Science Forum 185-188 (1995), pp. 91-98

Scharf, S.; Schmidt, M.; Bräunig, D.: Temperature Dependent Positive Oxide Charge Annealing by Electron Tunnelling. Semicond. Sci. Technol. 10 (1995), pp. 586-591

Schmidt, M.; Krankenhagen, R.; Sieber, I.; Henrion, W.: Mikrokristalline Siliziumschichten - Eigenschaften und Anwendung in Dünnschicht-solarzellen. Statusreport 1995 Photovoltaik, Eds.: BMFT, BEO, KFA Jülich

Sieber, I.; Schöpke, A.; Selle, B.: Comparative Composition Analysis of SiO<sub>x</sub> and SiN<sub>x</sub> by AES, EDX and RBS. Fresenius J. Anal. Chem. 353 (1995), pp. 639-641

Sieber, I.; Wanderka, N.; Urban, I.; Dörfel, I.: Elektronenmikroskopische Charakterisierung von mikrokristallinen Siliziumschichten. Beiträge zur Elektronenmikroskopischen Direktabbildung (BEDO 1995) Vol. 28 (1995), pp. 97-102 -g

**Sinh, N. D.; Füssel, W.; Flietner, H.:** Band Bending Bias Relation in Heteroemitter/c-Si Solar Cells from Modulation-CV Measurements. Proc. of the 13th European Photovoltaic Solar Energy Conference, Eds.: W. Freiesleben, W. Palz, H. A. Ossenbrink, P. Helm, Stephens & Ass., Bedford, UK (1995), pp. 1425-1427

**Wrana, M.; Schmidt, M.; Bräunig, D.:** Charge Storage Systems for Back Surface Field and Inversion Layer Solar Cells. Proc. of the 13th European Photovoltaic Solar Energy Conference, Eds.: W. Freiesleben, W. Palz, H. A. Ossenbrink, P. Helm, Stephens & Ass., Bedford, UK (1995), pp. 141-144

